Reconsideration of the rejection of claims 29-31 under 35 USC 102 as being anticipated by Sakakibara (US 5691560), is respectfully requested in view of the amended claims and for the reasons hereinafter given.

Claim 29 has been amended to incorporate the limitation cited in claim 30, and, accordingly, claim 30 has been cancelled. Thus, claim 29 now cites a lightly doped profile comprising phosphorous ions at a dosage level between about 1×10^{13} to 5×10^{13} atoms/cm². It is respectfully submitted that this is different from that is cited in the reference where the dosage is 1×10^{13} and 1×10^{15} atoms/cm² (column 10, line 26), and is highly doped at the 10^{15} level. It is believed that the base claim 29 is now allowable, and, hence claim 31 dependent from claim 29, and it is so requested, respectfully.

Allowance of all claims, as amended, is requested.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attachment is captioned "Version with Marking to Show Changes Made."

It is requested that should the Examiner not find that the Claims Allowable that are now presented, that he call the undersigned Attorney at 845/452-5863 to overcome any problems preventing allowance.

Respectfully submitted,

Stephen B. Ackerman, Reg. No: 37,761

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

A new title that is clearly indicative of the invention to which the claims are directed has been provided as follows:

"FLASH MEMORY WITH OPTIMUM IMPLANT ANGLE FOR DOUBLE DRAIN DOPING"

IN THE CLAIMS

Claim 29 has been amended as follows, and claim 30 cancelled:

- 29. A stacked gate having a doubly diffused drain (DDD) comprising:
- a junction having a lightly doped profile, the profile comprising phosphorous ions at a dosage level between about 1×10^{13} to 5×10^{13} atoms/cm²; and

a surface region having a heavily doped profile.

Claim 30 has been cancelled.